

IN THE CLAIMS

Per the revised amendment practice, a complete listing of all claims in the application follows.

Claim 1 (currently amended). A process for applying solutions on a semiconductor ~~wafer which comprises:~~ wafer, comprising:

- (a) rotating a substrate about a central point thereof;
- (b) dispensing a solution ~~mist~~ from a ~~spray~~ nozzle onto a top surface of said rotating substrate; and
moving said nozzle exclusively between a first point above said central point and a
- (c) ~~said dispensing nozzle moving radially between the central axis and an edge of the~~
second point above an edge of said substrate while dispensing said solution.

Claims 2-7 (cancelled).

8. (New) A method of coating a surface having an edge and a center, wherein said edge and said center define a radius, and wherein said surface spins around an axis through said center, said method comprising:

- providing a nozzle near said edge of said surface; and
- moving said nozzle along at most a portion of said radius.

9. (New) The method in claim 8, wherein said step of moving said nozzle further comprises moving said nozzle toward said center of said surface.

10. (New) The method in claim 9, wherein said step of moving said nozzle further comprises moving said nozzle toward a point external to said center.

11. (New) The method in claim 10, further comprising a step of dispersing a coating material from said nozzle during said step of moving said nozzle.

12. (New) A method of depositing a material at least partially along a diameter of a workpiece including a semiconductive material, said workpiece having an edge, a center, and an opposite edge, wherein said method comprises:

- providing a nozzle;
- positioning said nozzle generally over said edge of said workpiece including said semiconductive material;
- moving said nozzle in no more than one direction along said diameter; and
- spraying said material from said nozzle while moving said nozzle.

13. (Not entered).

14. (New) The method in claim 12, further comprising a step of stopping motion of said nozzle generally over said center.

15. (New) The method in claim 12, further comprising a step of stopping motion of said nozzle after said nozzle passes over said center.

16. (New) The method in claim 15, wherein said step of stopping motion of said nozzle further comprises stopping motion of said nozzle when said nozzle is over said opposite edge.

17. (New) A method of depositing a material at least partially along a diameter of a surface having an edge, a center, and an opposite edge, wherein said method comprises:

- rotating said surface;
- providing a nozzle;
- positioning said nozzle generally over said edge, wherein said step of positioning said nozzle generally over said edge further comprises:
 - positioning said nozzle over a first point along a circumference of said surface, and
 - defining said first point to be independent of a rotation of said surface;
- moving said nozzle in no more than one direction along said diameter;
- spraying said material from said nozzle while moving said nozzle; and

stopping motion of said nozzle after said nozzle passes over said center, wherein said step of stopping motion of said nozzle further comprises stopping motion of said nozzle when said nozzle is over said opposite edge, and wherein said step of stopping motion of said nozzle when said nozzle is over said opposite edge further comprises:

stopping motion of said nozzle over a second point along said circumference, and

defining said diameter with said first point, said center, and said second point.

18. (New) A method of coating a wafer with a solution, comprising:

generating a centrifugal force associated with said wafer;

spraying said solution from a nozzle onto said wafer; and

moving said nozzle while spraying, further comprising:

maintaining a generally constant direction of movement, and

moving said nozzle counter to said centrifugal force.

19. (New) The method in claim 18, wherein said step of moving said nozzle while spraying further comprises moving said nozzle concurrent with said centrifugal force.

20. (New) A method of propelling a nozzle over a spinning wafer, comprising:

initiating a motion of said nozzle in a first area concurrent with a generally greatest magnitude of centrifugal force on said wafer;

completing said motion in a second area concurrent with a generally least magnitude of centrifugal force on said wafer;

moving said nozzle through a third area between said initiating step and said completing step, wherein said third area is concurrent with a decreasing magnitude of centrifugal force; and

avoiding moving said nozzle through a fourth area concurrent with an increasing magnitude of centrifugal force while spraying a material from said nozzle.

21. (New) A method of moving a dispenser and a chuck, comprising:
defining a generally circular direction of rotation with said chuck; and
defining a generally non-reciprocal direction of motion with said dispenser,
further comprising:
facing a first side of said dispenser against said direction of
rotation, and
subsequently facing a second side of said dispenser against said
direction of rotation.
22. (New) The method in claim 21, wherein said step of defining a generally non-reciprocal
direction of motion with said dispenser further comprises defining a generally unidirectional line
of motion with said dispenser.
23. (New) A method of coating a wafer having a center, comprising:
providing an outward force from said wafer; and
spraying a mist from a source only while said source is moving counter to said
outward force.
24. (New) The method in claim 23, wherein said step of providing an outward force from said
wafer further comprises spinning said wafer around said center.
25. (New) A method of moving a chuck and a dispenser, comprising:
dispensing a fluid from said dispenser while said dispenser is moving in only one
direction from an initial position to a final position; and
rotating said chuck around a chuck center, further comprising:
defining a first region of said chuck moving toward said initial position,
defining a second region of said chuck next to said first region and moving
away from said initial position,
defining a third region of said chuck generally opposite from said first
region in relation to said chuck center and moving toward said final
position, and

defining a fourth region of said chuck generally opposite from said second region in relation to said chuck center and moving away from said final position.

26. (New) The method in claim 25, wherein said step of moving said dispenser further comprises intersecting an axis defined by said chuck center.

27. (New) The method in claim 26, wherein said step of moving said dispenser further comprises moving said dispenser over said chuck center.

28. (New) A method of moving an atomizer near a chuck, comprising:
defining a first plane with said chuck; and
passing said atomizer through a second plane generally parallel to said first plane,
wherein said passing step further comprises passing said atomizer at most once generally diametrically over said chuck.

29. (New) The method in claim 28, further comprising a step of partially defining a wafer site with said chuck, wherein said wafer site extends beyond said chuck; and wherein said step of passing said atomizer comprises passing said atomizer over said wafer site.

30. (New) A method of moving an atomizer near a chuck, comprising:
defining a first plane with said chuck;
partially defining a wafer site with said chuck, wherein said wafer site extends beyond said chuck; and
passing said atomizer through a second plane generally parallel to said first plane,
wherein said passing step further comprises passing said atomizer once generally diametrically over said chuck, and wherein said step of passing said atomizer once generally diametrically over said chuck further comprises passing said atomizer over said wafer site, and wherein said step of passing said atomizer over said wafer site further comprises passing said atomizer only over said wafer site.

Applicant notes that claim 13 as not been entered in order to maintain numbering continuity with the claims rejected in the grandparent application – ser. no. 09/292,081, filed 4/14/99 and issued as U.S. Pat. No. 6,423,380.